

IN THE CLAIMS:

Please cancel claims 2, 8, 10 and 16 without prejudice and amend the claims as follows:

1. (Currently Amended) A thermal shim adapted ~~for positioning~~ to be positioned between a wafer retention device and a pedestal, where~~in~~ said thermal shim comprises ~~a thermally insulative material~~ low-thermally-conductive-region centrally located within and a high thermally conductive region material.
2. (Cancelled)
3. (Currently Amended) The thermal shim of claim 1, wherein said ~~low thermally conductive region~~ insulative material is a hole.
4. (Currently Amended) The thermal shim of claim 1, wherein said ~~high thermally conductive region~~ material is in the shape of an annulus.
5. (Currently Amended) The thermal shim of claim 1, wherein the ~~high thermally conductive region~~ material is fabricated of a metallic material.
6. (Original) The thermal shim of claim 5 wherein said metallic material is aluminum or copper.
7. (Original) The thermal shim of claim 1 wherein the thermal shim is fabricated of a corrugated material.
8. (Cancelled)

9. (Currently Amended) A wafer support comprising:
a heat exchanger pedestal having a top surface;
a thermal shim having a thermally insulative material centrally disposed within a high thermally conductive region material and a low thermally conductive region; and
a wafer retention device having a bottom surface, wherein the thermal shim is located between the bottom surface of the wafer retention device and the top surface of the heat exchanger pedestal.
10. (Cancelled)
11. (Currently Amended) The wafer support of claim 9, wherein said ~~low thermally conductive region~~ insulative material is a hole.
12. (Currently Amended) The wafer support of claim 9, wherein said ~~high thermally conductive region~~ material is in the shape of an annulus.
13. (Currently Amended) The wafer support of claim 9, wherein the ~~high thermally conductive region~~ material is fabricated of a metallic material.
14. (Original) The wafer support of claim 13 wherein said metallic material is aluminum or copper.
15. (Original) The wafer support of claim 9 wherein the thermal shim is fabricated of a corrugated material.
16. (Cancelled)
17. (Currently Amended) An etch reactor having a wafer support, wherein said wafer support comprises:
a heat exchanger pedestal having a top surface;

a thermal shim having a thermally insulative material centrally disposed within an annular shaped a-high thermally conductive region material and a centrally located hole defined by the high thermally conductive region; and

an electrostatic chuck having a bottom surface, wherein the thermal shim is located between the bottom surface of the electrostatic chuck and the top surface of the heat exchanger pedestal.

18. (Currently Amended) The etch reactor of claim 1, wherein the thermal shim is fabricated of metal.

19. (Currently Amended) The etch reactor of claim 1, wherein the thermal shim is corrugated.

20. (Currently Amended) A wafer support comprising:

a heat exchanger pedestal having a top surface;

means for controlling thermal conductivity having a thermally insulative material centrally disposed within a high thermally conductive material region and a low thermally conductive region; and

a wafer retention device having a bottom surface, wherein the means for controlling thermal conductivity is located between the bottom surface of the wafer retention device and the top surface of the heat exchanger pedestal.

21. (Original) The wafer support of claim 20 wherein said means for controlling the thermal conductivity is a thermal shim.

Please add the following new claims:

22. (New) A thermal shim adapted to be positioned between a wafer retention device and a pedestal, wherein the thermal shim comprises a thermally conductive material centrally located within a thermally insulative material.

23. (New) The thermal shim of claim 22, wherein the thermally insulative material is in the shape of an annulus.

24. (New) The thermal shim of claim 22, wherein the thermally conductive material is fabricated of a metallic material.

25. (New) The thermal shim of claim 24, wherein the metallic material is made from aluminum or copper.

26. (New) A wafer support, comprising:
a heat exchanger pedestal having a top surface;
a thermal shim having a thermally conductive material centrally disposed within a thermally insulative material; and
a wafer retention device having a bottom surface, wherein the thermal shim is located between the bottom surface of the wafer retention device and the top surface of the heat exchanger pedestal.

27. (New) The wafer support of claim 26, wherein the thermally insulative material is in the shape of an annulus.

28. (New) The wafer support of claim 26, wherein the thermally conductive material is fabricated of a metallic material.

29. (New) The wafer support of claim 26, wherein the metallic material is made from aluminum or copper.